

## Product Summary

$V_{(BR)DSS}$	$R_{DS(ON)}$ max	$I_D$ max $T_A = +25^\circ\text{C}$
-20V	120m $\Omega$ @ $V_{GS} = -4.5\text{V}$	-3A
	150m $\Omega$ @ $V_{GS} = -2.5\text{V}$	

## Description and Applications

This MOSFET is designed to minimize the on-state resistance ( $R_{DS(ON)}$ ) and yet maintain superior switching performance, making it ideal for high efficiency power management applications.

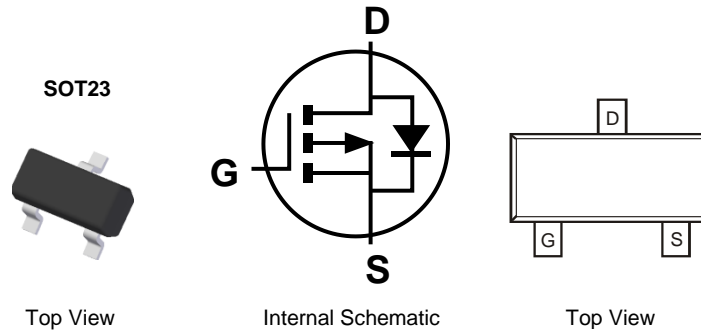
- Backlighting
- Power Management Functions
- DC-DC Converters
- Motor Control

## Features and Benefits

- Low On-Resistance
- Low Input Capacitance
- Fast Switching Speed
- **Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)**
- **Halogen and Antimony Free. "Green" Device (Note 3)**

## Mechanical Data

- Case: SOT23
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish — Matte Tin Annealed over Copper Leadframe. Solderable per MIL-STD-202, Method 208
- Terminals Connections: See Diagram Below
- Weight: 0.008 grams (Approximate)

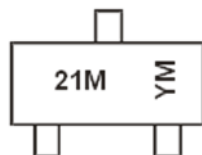
**NEW PRODUCT**


## Ordering Information (Note 4)

Part Number	Case	Packaging
DMG2301L-7	SOT23	3,000/Tape & Reel
DMG2301L-13	SOT23	10,000/Tape & Reel

- Notes:
1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant.
  2. See [http://www.diodes.com/quality/lead\\_free.html](http://www.diodes.com/quality/lead_free.html) for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
  3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
  4. For packaging details, go to our website at <http://www.diodes.com/products/packages.html>.

## Marking Information



21M = Product Type Marking Code  
 YM = Date Code Marking  
 Y or  $\bar{Y}$  = Year (ex: C = 2015)  
 M = Month (ex: 9 = September)

### Date Code Key

Year	2014	2015	2016	2017	2018	2019	2020
Code	B	C	D	E	F	G	H

Month	Jan	Feb	Mar	Apr	May	Jun	Jul	Aug	Sep	Oct	Nov	Dec
Code	1	2	3	4	5	6	7	8	9	O	N	D

**Maximum Ratings** (@T<sub>A</sub> = +25°C, unless otherwise specified)

Characteristic			Symbol	Value	Units
Drain-Source Voltage			V <sub>DSS</sub>	-20	V
Gate-Source Voltage			V <sub>GSS</sub>	±8	V
Continuous Drain Current (Note 5) V <sub>GS</sub> = -4.5V	Steady State	T <sub>A</sub> = +25°C	I <sub>D</sub>	-3	A
		T <sub>A</sub> = +70°C		-1	A
Pulsed Drain Current (Note 6)			I <sub>DM</sub>	-10	A
Drain-Source Diode Forward Current (t < 5 sec)			I <sub>S</sub>	-0.75	A

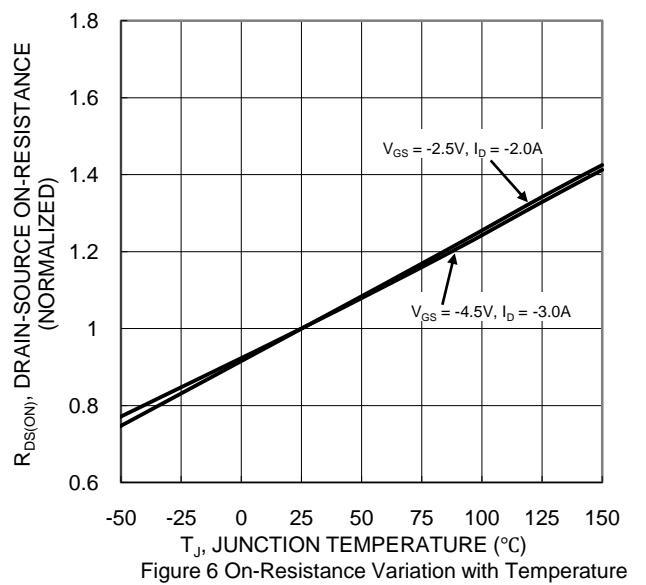
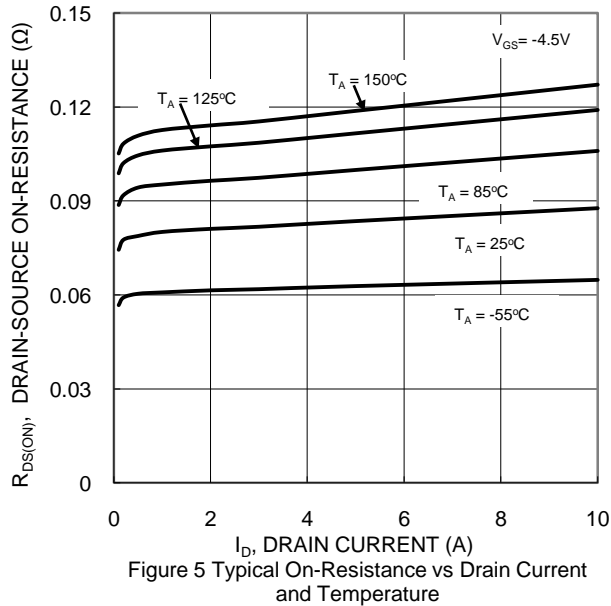
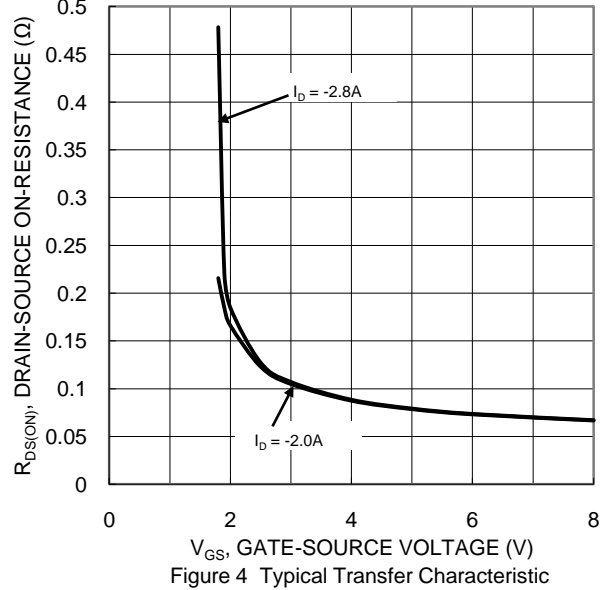
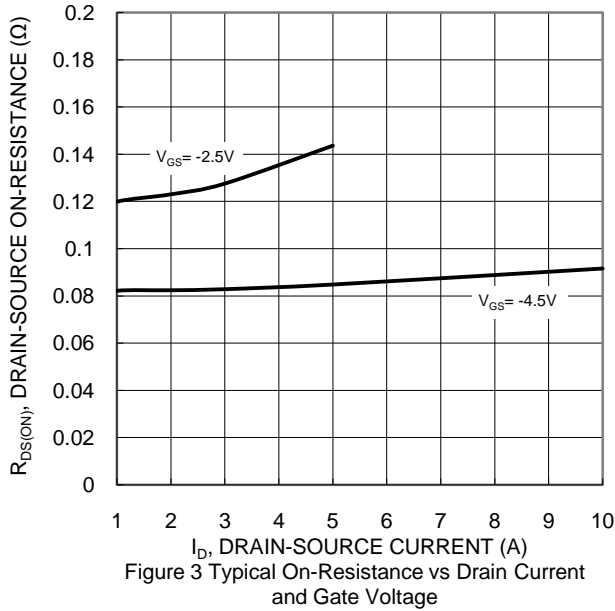
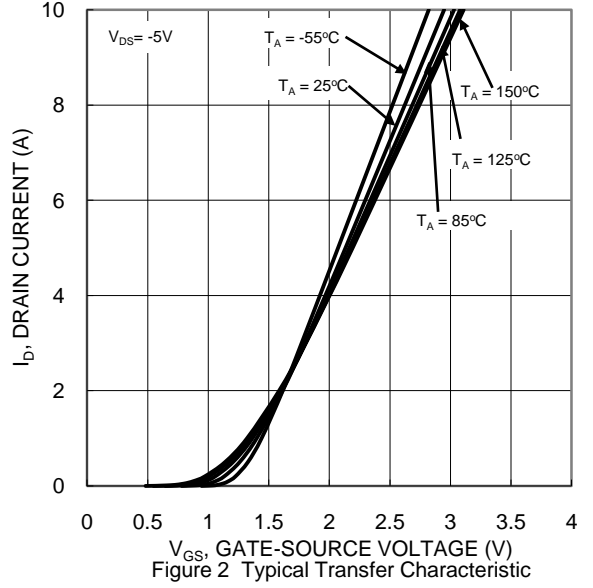
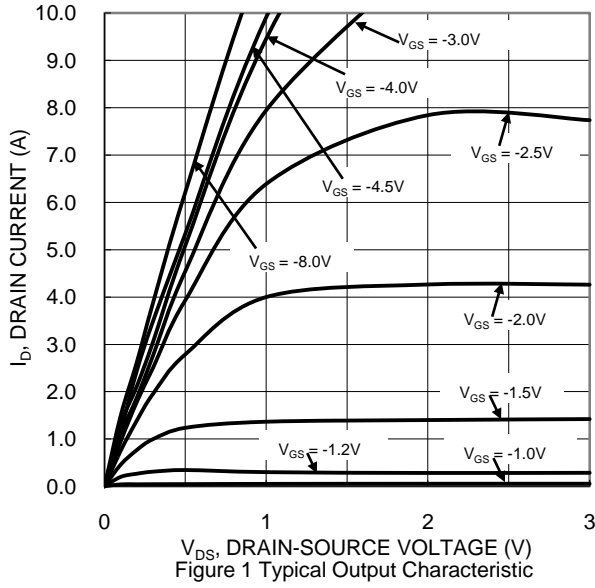
**Thermal Characteristics**

Characteristic	Symbol	Value	Unit
Power Dissipation (Note 5)	P <sub>D</sub>	1.5	W
Thermal Resistance, Junction to Ambient @T <sub>A</sub> = +25°C (Note 5)	R <sub>θJA</sub>	83	°C/W
Operating and Storage Temperature Range	T <sub>J</sub> , T <sub>STG</sub>	-55 to +150	°C

**Electrical Characteristics** (@T<sub>A</sub> = +25°C, unless otherwise specified)

Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition
<b>OFF CHARACTERISTICS (Note 7)</b>						
Drain-Source Breakdown Voltage	BV <sub>DSS</sub>	-20	—	—	V	V <sub>GS</sub> = 0V, I <sub>D</sub> = -250μA
Zero Gate Voltage Drain Current T <sub>J</sub> = +25°C	I <sub>DSS</sub>	—	—	-1.0	μA	V <sub>DS</sub> = -16V, V <sub>GS</sub> = 0V
Gate-Source Leakage	I <sub>GSS</sub>	—	—	±100	nA	V <sub>GS</sub> = ±6V, V <sub>DS</sub> = 0V
<b>ON CHARACTERISTICS (Note 7)</b>						
Gate Threshold Voltage	V <sub>GS(TH)</sub>	-0.4	—	-1.2	V	V <sub>DS</sub> = V <sub>GS</sub> , I <sub>D</sub> = -250μA
Static Drain-Source On-Resistance	R <sub>DS(ON)</sub>	—	—	120	mΩ	V <sub>GS</sub> = -4.5V, I <sub>D</sub> = -2.8A
				150		V <sub>GS</sub> = -2.5V, I <sub>D</sub> = -2.0A
Diode Forward Voltage	V <sub>SD</sub>	—	—	-1.2	V	V <sub>GS</sub> = 0V, I <sub>S</sub> = -0.75A
<b>DYNAMIC CHARACTERISTICS (Note 8)</b>						
Input Capacitance	C <sub>iss</sub>	—	476	—	pF	V <sub>DS</sub> = -10V, V <sub>GS</sub> = 0V f = 1.0MHz
Output Capacitance	C <sub>oss</sub>	—	53	—	pF	
Reverse Transfer Capacitance	C <sub>rss</sub>	—	45	—	pF	
Total Gate Charge	Q <sub>g</sub>	—	5.5	—	nC	V <sub>GS</sub> = -4.5V, V <sub>DS</sub> = -6V, I <sub>D</sub> = -2.8A
Gate-Source Charge	Q <sub>gs</sub>	—	0.9	—	nC	
Gate-Drain Charge	Q <sub>gd</sub>	—	1.8	—	nC	
Turn-On Delay Time	t <sub>D(ON)</sub>	—	5	—	ns	V <sub>DS</sub> = -6V, V <sub>GS</sub> = -4.5V, R <sub>GEN</sub> = 6Ω, I <sub>D</sub> = -1A
Turn-On Rise Time	t <sub>R</sub>	—	10	—	ns	
Turn-Off Delay Time	t <sub>D(OFF)</sub>	—	30	—	ns	
Turn-Off Fall Time	t <sub>F</sub>	—	20	—	ns	

- Notes:
- Device mounted on 1" x 1" FR-4 PCB with high coverage 2oz. Copper, single sided.
  - Repetitive rating, pulse width limited by junction temperature.
  - Short duration pulse test used to minimize self-heating effect.
  - Guaranteed by design. Not subject to production testing.



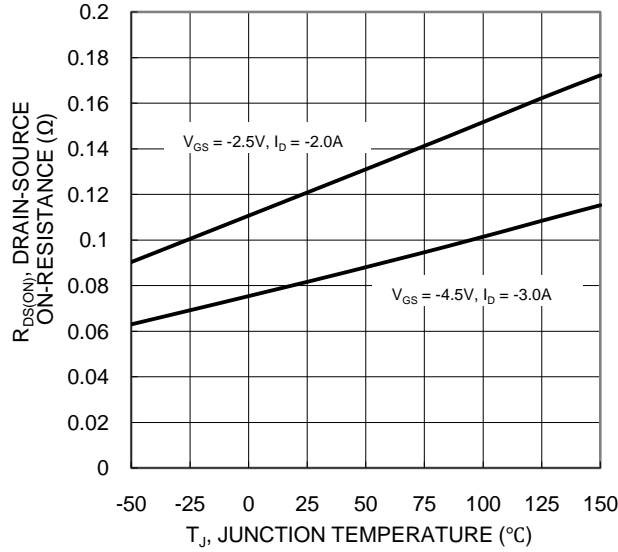


Figure 7 On-Resistance Variation with Temperature

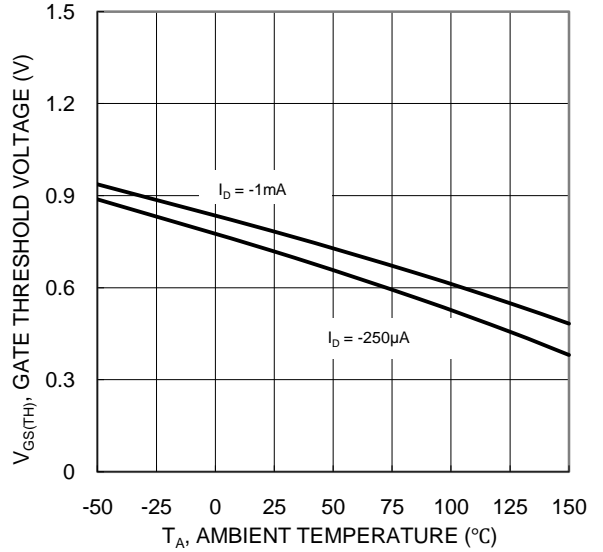


Figure 8 Gate Threshold Variation vs Ambient Temperature

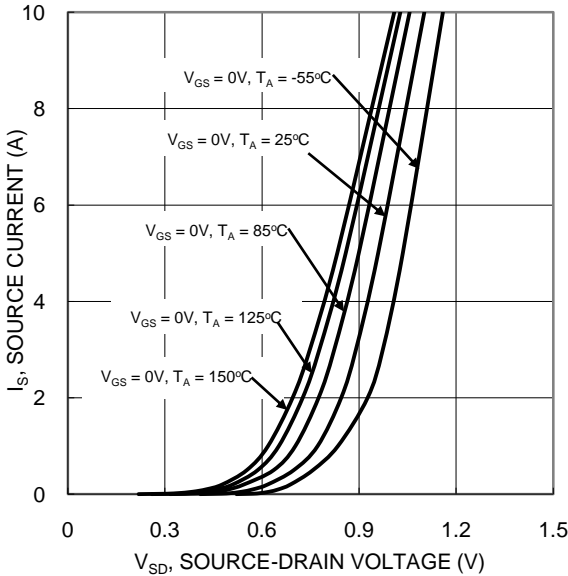


Figure 9 Diode Forward Voltage vs. Current

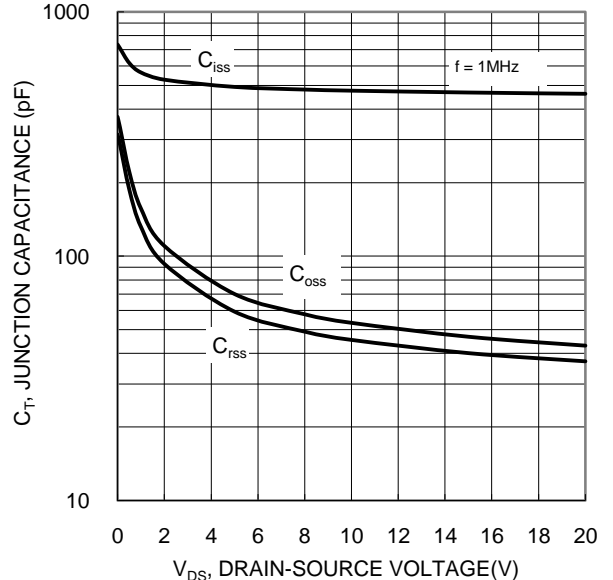


Figure 10 Typical Junction Capacitance

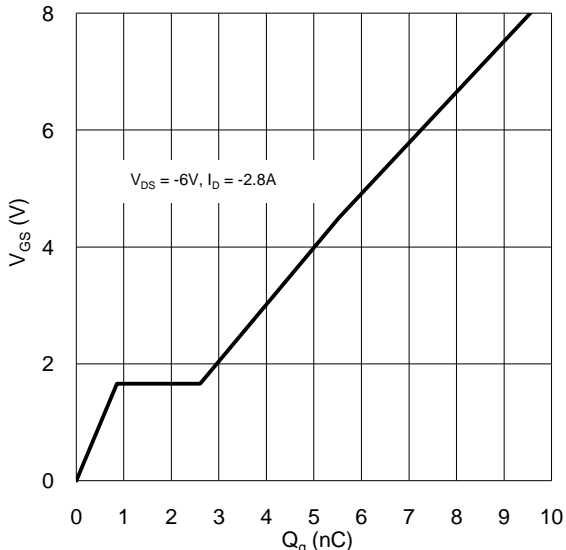


Figure 11 Gate Charge

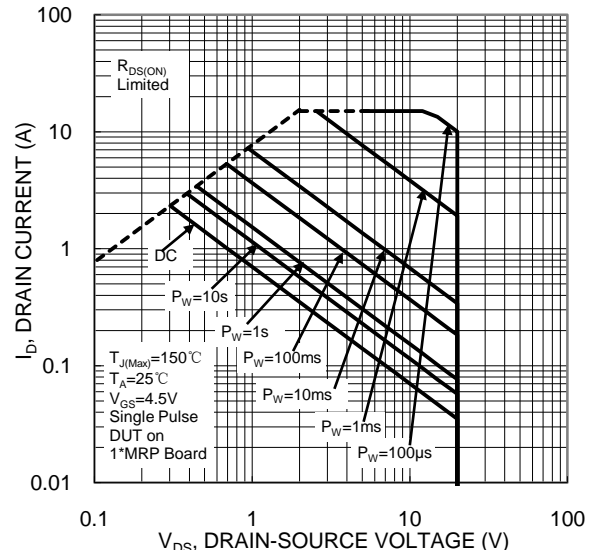


Figure 12 SOA, Safe Operation Area

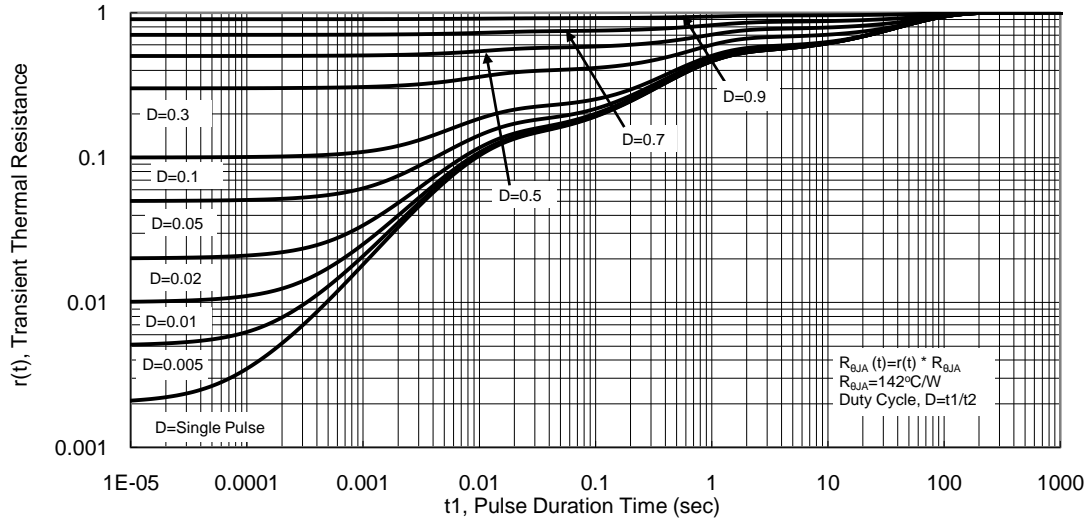
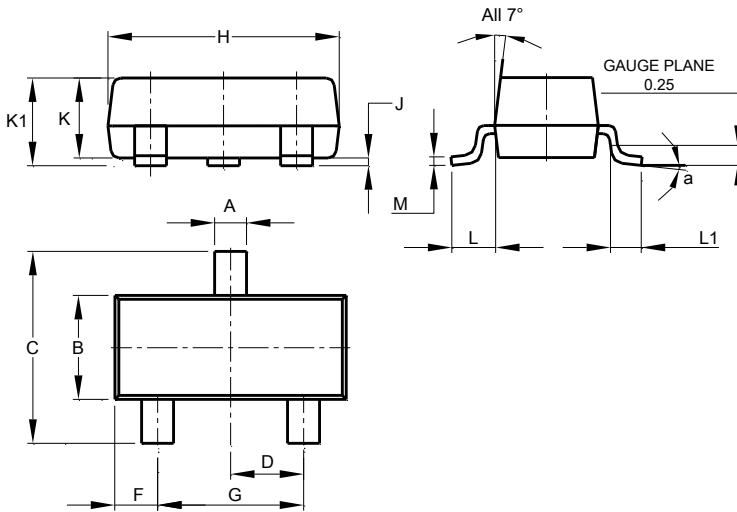


Figure 13 Transient Thermal Resistance

### Package Outline Dimensions

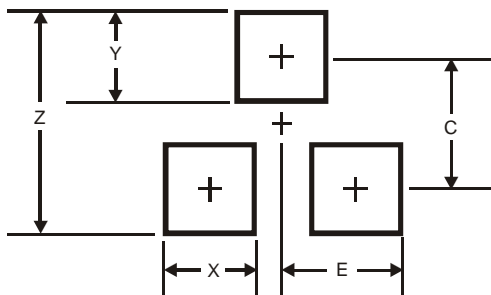
Please see AP02002 at <http://www.diodes.com/datasheets/ap02002.pdf> for the latest version.



SOT23			
Dim	Min	Max	Typ
A	0.37	0.51	0.40
B	1.20	1.40	1.30
C	2.30	2.50	2.40
D	0.89	1.03	0.915
F	0.45	0.60	0.535
G	1.78	2.05	1.83
H	2.80	3.00	2.90
J	0.013	0.10	0.05
K	0.890	1.00	0.975
K1	0.903	1.10	1.025
L	0.45	0.61	0.55
L1	0.25	0.55	0.40
M	0.085	0.150	0.110
a	8°		
All Dimensions in mm			

### Suggested Pad Layout

Please see AP02001 at <http://www.diodes.com/datasheets/ap02001.pdf> for the latest version.



Dimensions	Value (in mm)
Z	2.9
X	0.8
Y	0.9
C	2.0
E	1.35

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